

An ISO/TS16949 and ISO 9001 Certified Company



SILICON POWER SWITCHING TRANSISTORS



2N5320, 2N5321 NPN 2N5322, 2N5323 PNP

TO-39 Metal Can Package

Medium Power Amplifier and Switching Applications

ABSOLUTE MAXIMUM RATINGS

DESCRIPTION	SYMBOL	2N5320	2N5321	2N5322	2N5323	UNITS
Collector Emitter Voltage	V _{CEO}	75	50	75	50	V
Collector Base Voltage	V _{CBO}	100	75	100	75	V
Emitter Base Voltage	V _{EBO}	7	5	7	5	V
Collector Current - Continuous	I _C	2.0				Α
Base Current	I _B	1.0				А
Power Dissipation@ T _a =25°C	P _D	1				
Derate Above 25°C		5.71				
Power Dissipation@ T _c =25°C	P_{D}	10			W	
Derate Above 25°C		57.14			mW/ ºC	
Operating And Storage Junction Temperature Range	T_{j}, T_{stg}	- 65 to +200				°C

THERMAL CHARACTERISTICS

Junction to Ambient in free air	R _{th (j-a)}	175	°C/W
Junction to Case	R _{th (i-c)}	17.5	°C/W

ELECTRICAL CHARACTERISTICS (T_a=25°C unless specified otherwise)

DESCRIPTION	SYMBOL	TEST CONDITION MIN		MAX	UNITS
Collector Emitter Voltage	V_{CEO}	I _C =100mA, I _B =0			
_		2N5320/5322	75		V
		2N5321/5323	50		V
Collector Cut Off Current	I _{CEX}	V _{CE} =70V, V _{BE} =1.5V, T _c =150°C		5	
		2N5320/5322		5	mA
		V _{CE} =45V, V _{BE} =1.5V, T _c =150°C			
		2N5321/5323	5	mA	
		211002170020			
		V _{CE} =100V, V _{BE} =1.5V		400	
		2N5320/5322		100	μΑ
		V _{CE} =75V, V _{BE} =1.5V		400	
		2N5321/5323	100		μΑ
Emitter Cut Off Current	urrent I_{EBO} $V_{BE}=5V$, $I_{C}=0$			100	^
		2N5321/5323		100	μΑ
		$V_{BE}=7V$, $I_{C}=0$		400	
		52 0		100	μΑ
		2N5320/5322			

SILICON POWER SWITCHING TRANSISTORS



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800

1000

ns

ns

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ELECTRICAL CHARACTERISTICS (T_a=25°C unless specified otherwise)

DESCRIPTION	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNITS
DC Current Gain	*h _{FE}	I _C =1A, V _{CE} =2V				
		2N5320/5322	10			
		I _C =0.5A, V _{CE} =4V				
		2N5320/5322	30		130	
		2N5321/5323	40		250	
Collector Emitter Saturation Voltage	*V _{CE (sat)}	I _C =500mA, I _B =50mA				
		2N5320			0.5	V
		2N5321			8.0	V
		2N5322			0.7	V
		2N5323			1.2	V
Base Emitter On Voltage	*V _{BE (on)}	$I_C=500$ mA, $V_{CE}=4$ V				
		2N5320/5322			1.1	V
		2N5321/5323			1.4	V
DYNAMIC CHARACTERISTICS						
Small Signal Current Gain	h _{fe}	I _C =50mA,V _{CE} =4V, f=10MHz	5			
SWITCHING CHARACTERISTICS						
Turn On time	t _{on}	V_{CC} =30V, I_{C} =500mA, I_{B1} =50mA				
		2N5320/5321			80	ns
		2N5322/5323			100	ns
Turn Off time	t _{off}	$V_{CC}=30V$, $I_{C}=500$ mA, $I_{B1}=I_{B2}=50$ mA				

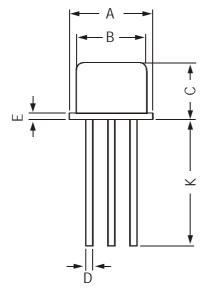
2N5320/5321

2N5322/5323

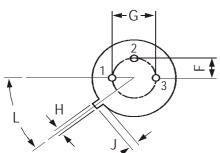
^{*}Pulsed: Pulse width \leq 300ms, duty cycle \leq 2%

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DIM	MIN	MAX
Α	8.50	9.39
В	7.74	8.50
С	6.09	6.60
D	0.40	0.53
Ε	_	0.88
F	2.41	2.66
G	4.82	5.33
Н	0.71	0.86
J	0.73	1.02
Κ	12.70	_
L	42 DEG	48 DEG
L	42 DEG	48 DEG





All dimensions are in mm

PIN CONFIGURATION

- 1. EMITTER
- 2. BASE
- 3. COLLECTOR

Packing Details

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/Qty	Size	Qty	Size	Qty	GrWt
TO-39	500 pcs/polybag	540 gm/500 pcs	3" x 7.5" x 7.5"	20K	17" x 15" x 13.5"	32K	40 kgs

Notes

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Disclaimer

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